FAIRCHILD SEMICONDUCTOR®

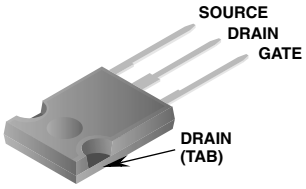
January 2002

IRFP250N

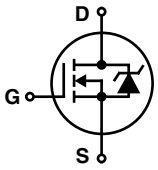
N-Channel Power MOSFET
200V, 30A, 0.075Ω

Features

- Ultra Low On-Resistance
  - $r_{DS(ON)}$ = 0.052Ω (Typ), V_{GS} = 10V
- Simulation Models
  - Temperature Compensated PSPICE® and SABER© Electrical Models
  - Spice and SABER© Thermal Impedance Models
- Peak Current vs Pulse Width Curve
- UIS Rating Curve



TO-247



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	200	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current		
	Continuous (T_C = 25°C, V_{GS} = 10V)	30	A
	Continuous (T_C = 100°C, V_{GS} = 10V)	21	A
	Pulsed	Figure 4	A
E_{AS}	Single Pulse Avalanche Energy (Note 1)	315	mJ
P_D	Power dissipation	214	W
	Derate above 25°C	1.4	W/°C
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case TO-247	0.70	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-247	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
IRFP250N	IRFP250N	TO-247	Tube	N/A	30

Electrical Characteristics T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
Off Characteristics							
B_{VDSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V		200	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 200V	V_{GS} = 0V	-	-	25	μA
		V_{DS} = 160V	T_C = 150°C	-	-	250	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V		-	-	±100	nA
On Characteristics							
$V_{GS(TH)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA		2	-	4	V
$r_{DS(ON)}$	Drain to Source On Resistance	I_D = 18A, V_{GS} = 10V		-	0.052	0.075	Ω
g_{fs}	Forward Transconductance	V_{DS} = 50V, I_D = 18A (Note 2)		17	-	-	S
Dynamic Characteristics							
C_{ISS}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz		-	4023	-	pF
C_{OSS}	Output Capacitance			-	880	-	pF
C_{RSS}	Reverse Transfer Capacitance			-	240	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 20V	V_{GS} = 0V to 20V	V_{DD} = 160V, I_D = 18A, I_g = 2.0mA		215	280	nC
$Q_{g(10)}$	Total Gate Charge at 10V	V_{GS} = 0V to 10V		-	114	140	nC
$Q_{g(TH)}$	Threshold Gate Charge	V_{GS} = 0V to 2V		-	8	10	nC
Q_{gs}	Gate to Source Gate Charge			-	14	-	nC
Q_{gd}	Gate to Drain “Miller” Charge			-	44	-	nC
Switching Characteristics (V_{GS} = 10V)							
t_{ON}	Turn-On Time	V_{DD} = 100V, I_D = 18A, V_{GS} = 10V, R_{GS} = 3.9Ω		-	-	69	ns
$t_{d(ON)}$	Turn-On Delay Time			-	16	-	ns
t_r	Rise Time			-	30	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time			-	78	-	ns
t_f	Fall Time			-	40	-	ns
t_{OFF}	Turn-Off Time			-	-	177	ns
Drain-Source Diode Characteristics							
V_{SD}	Source to Drain Diode Voltage	I_{SD} = 18A		-	-	1.3	V
t_{rr}	Reverse Recovery Time	I_{SD} = 18A, dI_{SD}/dt = 100A/μs		-	-	279	ns
Q_{RR}	Reverse Recovered Charge	I_{SD} = 18A, dI_{SD}/dt = 100A/μs		-	-	2000	nC

Notes:
1: Starting T_J = 25°C, L = 1.9mH, I_{AS} = 18A.
2: Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristic

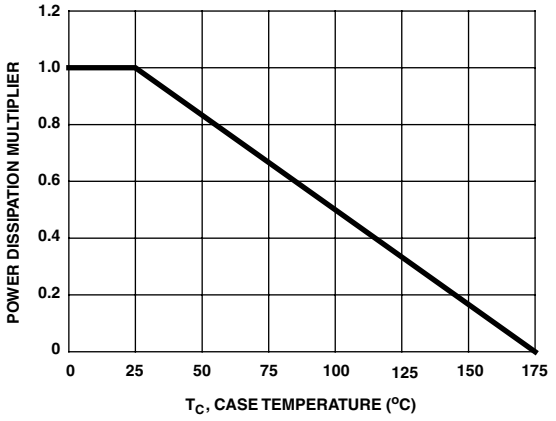


Figure 1. Normalized Power Dissipation vs Ambient Temperature

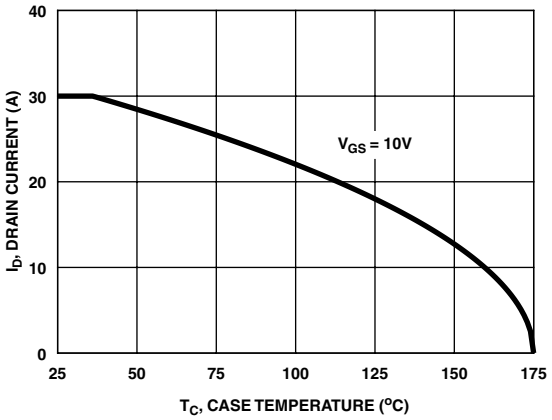


Figure 2. Maximum Continuous Drain Current vs Case Temperature

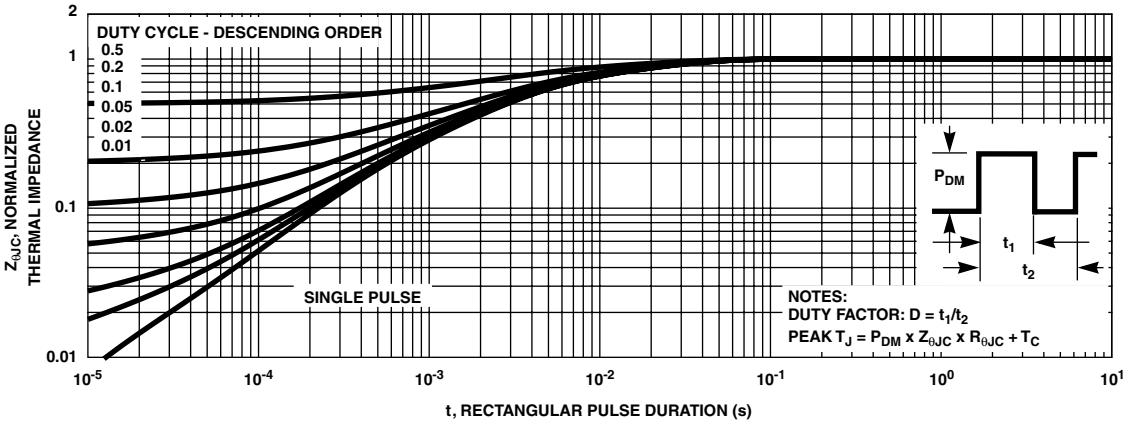


Figure 3. Normalized Maximum Transient Thermal Impedance

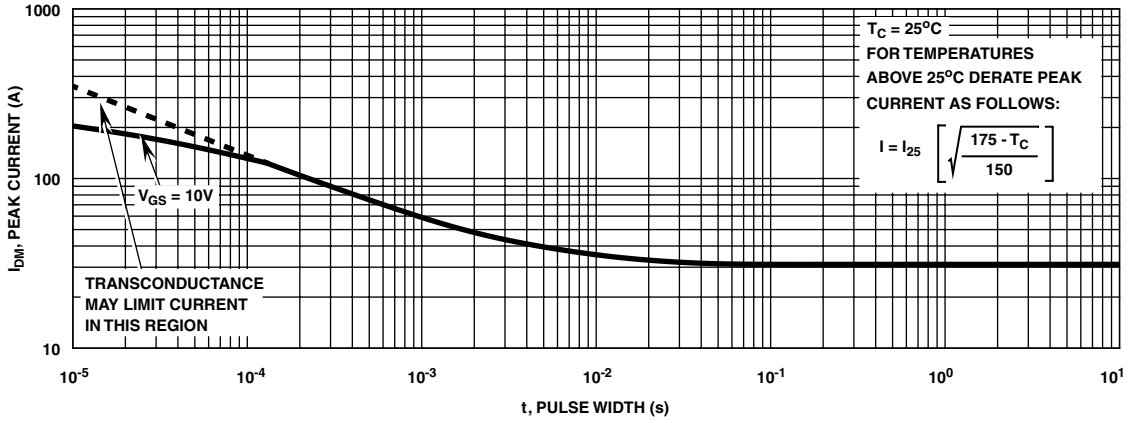


Figure 4. Peak Current Capability

Typical Characteristic (Continued)

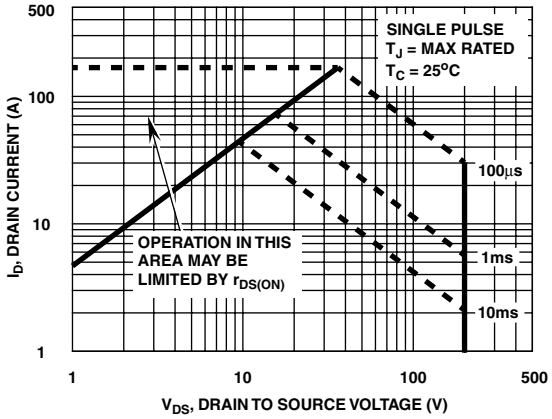


Figure 5. Forward Bias Safe Operating Area

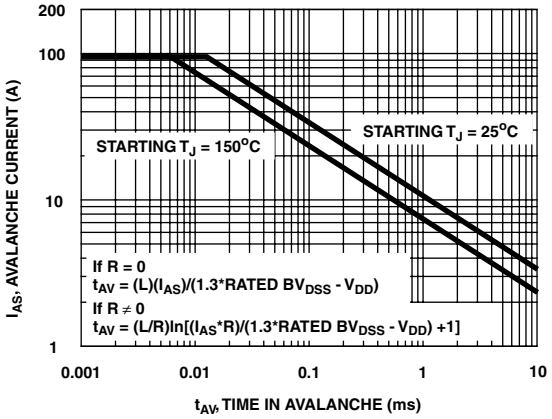


Figure 6. Unclamped Inductive Switching Capability

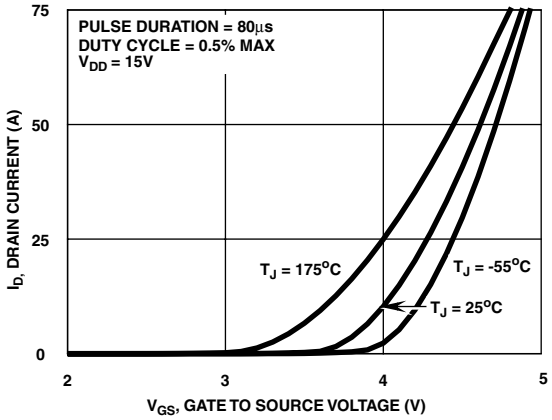


Figure 7. Transfer Characteristics

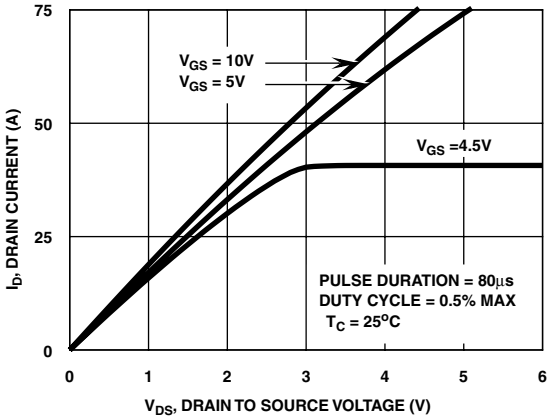


Figure 8. Saturation Characteristics

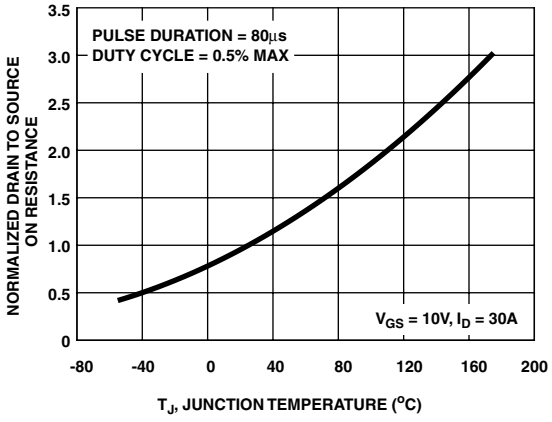


Figure 9. Normalized Drain to Source On Resistance vs Junction Temperature

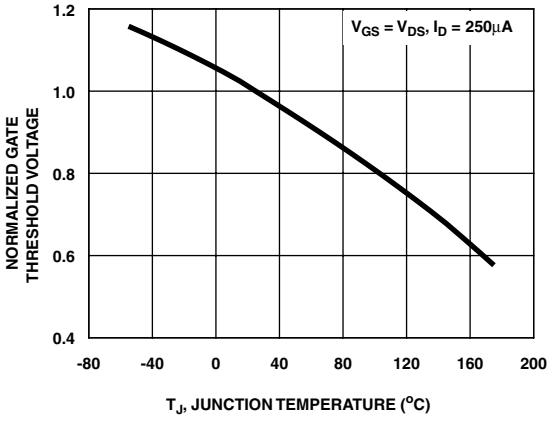


Figure 10. Normalized Gate Threshold Voltage vs Junction Temperature

Typical Characteristic (Continued)

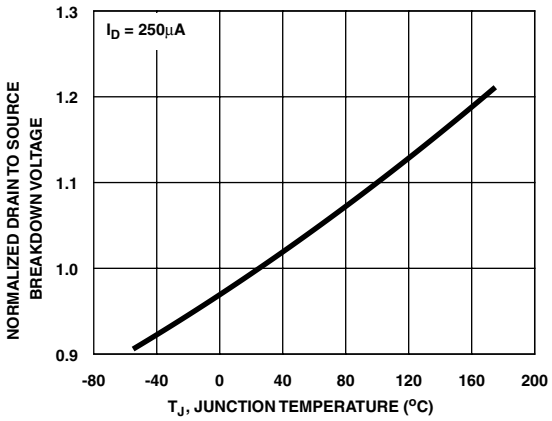


Figure 11. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

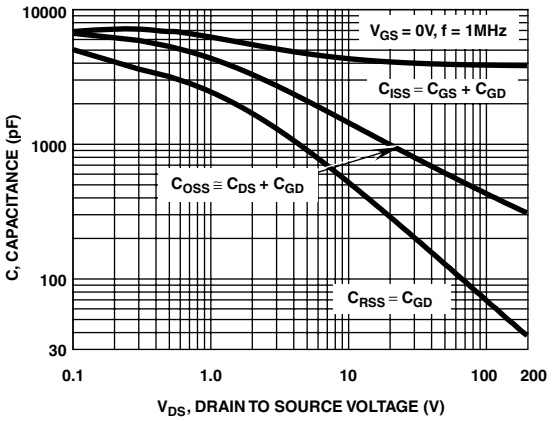


Figure 12. Capacitance vs Drain to Source Voltage

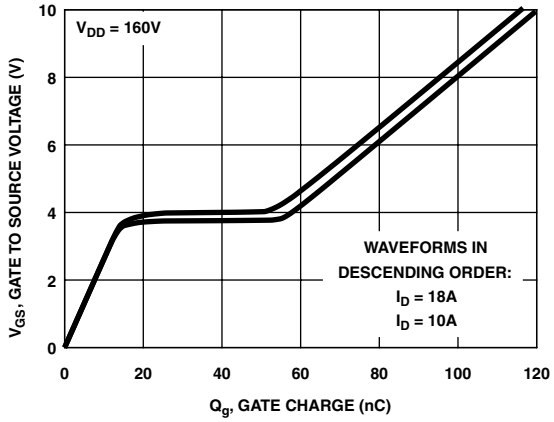


Figure 13. Gate Charge Waveforms for Constant Gate Currents

Test Circuits and Waveforms

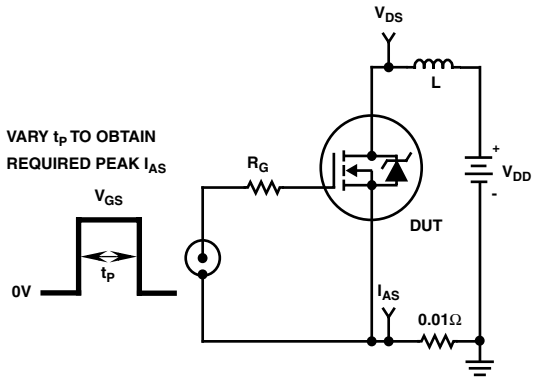


Figure 14. Unclamped Energy Test Circuit

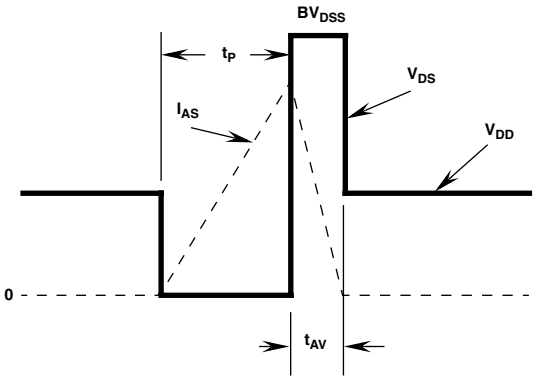


Figure 15. Unclamped Energy Waveforms

Test Circuits and Waveforms (Continued)

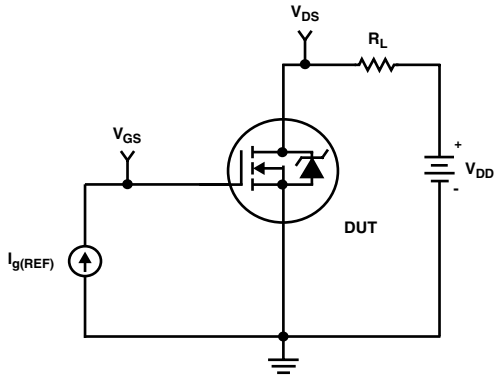


Figure 16. Gate Charge Test Circuit

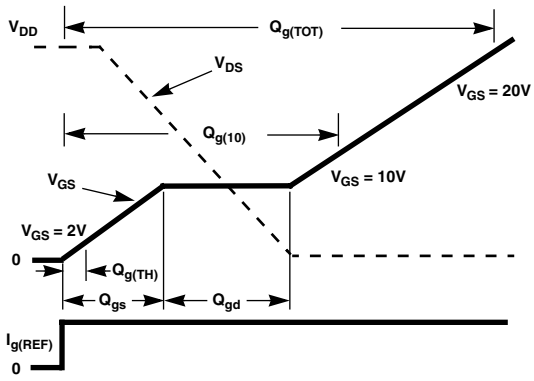


Figure 17. Gate Charge Waveforms

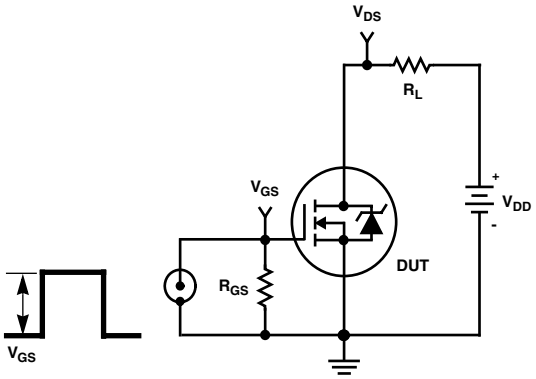


Figure 18. Switching Time Test Circuit

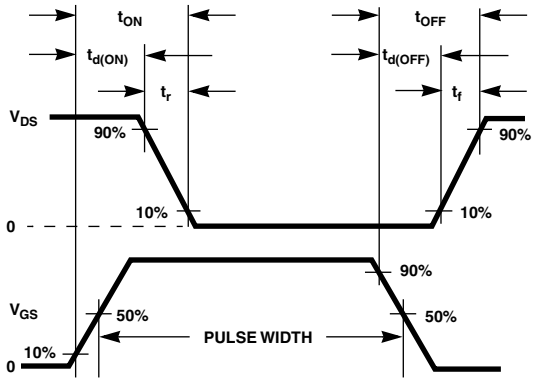
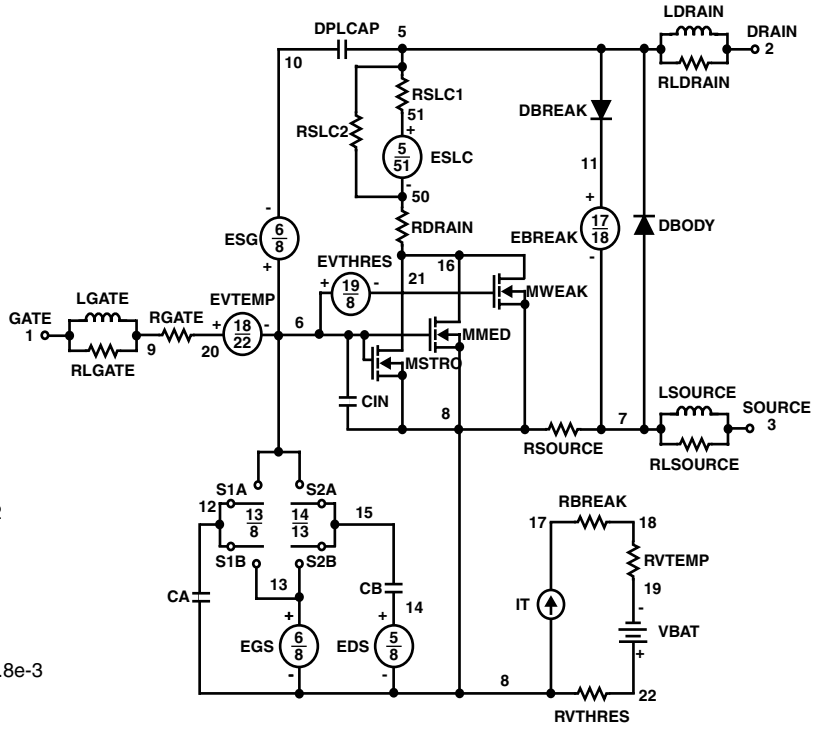


Figure 19. Switching Time Waveforms

PSPICE Electrical Model

```
.SUBCKT IRFP250N 2 1 3 ;       rev May 2001

CA  12 8 6.6e-9
CB  15 14 6.5e-9
CIN  6 8 3.80e-9

DBODY 7 5 DBODYMOD
DBREAK 5 11  DBREAKMOD
DPLCAP 10 5 DPLCAPMOD

EBREAK 11 7 17  18 221
EDS  14  8  5  8 1
EGS  13  8  6  8 1
ESG 6 10 6 8 1
EVTHRES 6 21 19 8  1
EVTEMP 20 6 18 22 1

IT  8  17  1

LDRAIN 2 5 1.0e-9
LGATE 1  9 8.05e-9
LSOURCE  3  7 5.8e-9

MMED 16 6 8 8 MMEDMOD
MSTRO 16 6 8 8 MSTROMOD
MWEAK 16 21 8 8 MWEAKMOD

RBREAK  17  18  RBREAKMOD  1
RDRAIN 50 16 RDRAINMOD 5.0e-2
RGATE  9  20 0.77
RLDRAIN 2 5 10
RLGATE 1 9 80.5
RLSOURCE 3 7 58
RSLC1 5 51 RSLCMOD 1e-6
RSLC2 5 50 1e3
RSOURCE  8  7  RSOURCEMOD 1.8e-3
RVTHRES 22 8 RVTHRESMOD  1
RVTEMP 18 19 RVTEMPMOD 1

S1A  6  12  13  8  S1AMOD
S1B  13  12  13  8  S1BMOD
S2A  6  15  14  13  S2AMOD
S2B  13  15  14  13  S2BMOD

VBAT 22 19  DC  1

ESLC 51 50 VALUE={(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)/(1e-6*100),2.5))}

.MODEL DBODYMOD D (IS = 2.8e-12 RS = 3.0e-3  XTI = 5.5 TRS1 = 3.5e-3  TRS2 = 1e-5  CJO = 2.55e-9  TT = 1.52e-7 M = 0.42)
.MODEL DBREAKMOD D (RS = 1.2e-0  TRS1 = 1e-3  TRS2 = 1e-6)
.MODEL DPLCAPMOD D (CJO = 4.6e-9  IS = 1e-30 N = 10 M = 0.9)
.MODEL MMEDMOD NMOS (VTO = 3.05 KP = 2.5 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 0.77)
.MODEL MSTROMOD NMOS (VTO = 3.55 KP = 100 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)
.MODEL MWEAKMOD NMOS (VTO = 2.69 KP = 0.05 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 7.70 )
.MODEL RBREAKMOD RES (TC1 =1.27e-3  TC2 = 1.0e-6)
.MODEL RDRAINMOD RES (TC1 = 9.90e-3  TC2 = 3.60e-5)
.MODEL RSLCMOD RES (TC1 = 3.0e-3 TC2 = 1.0e-6)
.MODEL RSOURCEMOD RES (TC1 = 1e-3 TC2 = 1e-6)
.MODEL RVTHRESMOD RES (TC1 = -2.90e-3 TC2 = -1.10e-5)
.MODEL RVTEMPMOD RES (TC1 = -2.80e-3  TC2 = 1.70e-7)

.MODEL S1AMOD VSWITCH (RON = 1e-5  ROFF = 0.1  VON = -5.5  VOFF= -4.5)
.MODEL S1BMOD VSWITCH (RON = 1e-5  ROFF = 0.1  VON = -4.5  VOFF= -5.5)
.MODEL S2AMOD VSWITCH (RON = 1e-5  ROFF = 0.1  VON = -0.3  VOFF= 0.4)
.MODEL S2BMOD VSWITCH (RON = 1e-5  ROFF = 0.1  VON = 0.4  VOFF= -0.3)

.ENDS
```

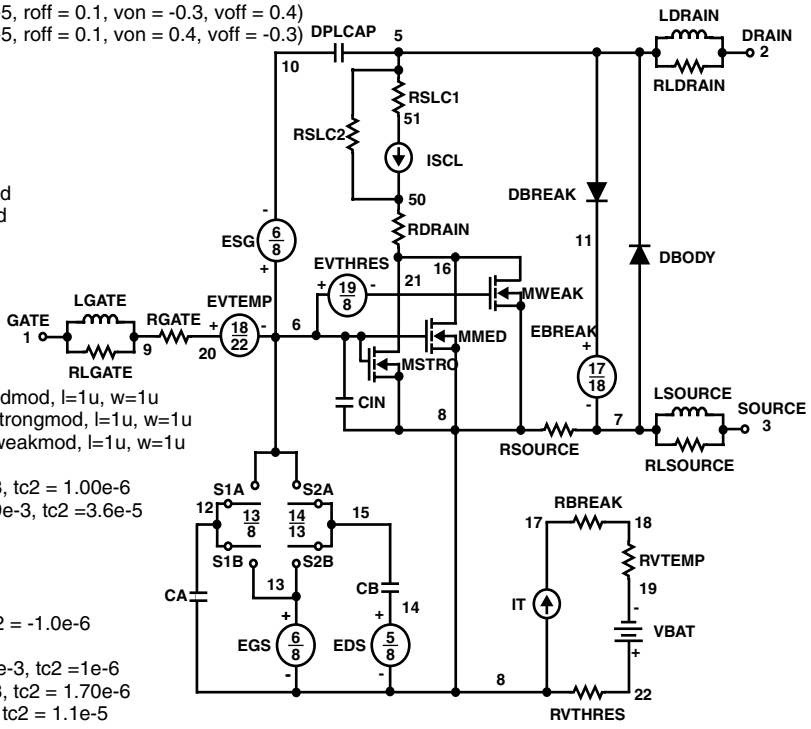


NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.

SABER Electrical Model

REV May 2001

```
template IRFP250N n2,n1,n3
electrical n2,n1,n3
{
var i iscl
dp..model dbodymod =  (isl = 2.8e-12, rs = 3.0e-3, xti = 5.5, trs1 = 3.5e-3, trs2 = 1.0e-5, cjo = 2.55e-9, tt = 1.52e-7, m = 0.42)
dp..model dbreakmod = (rs = 1.2, trs1 = 1.0e-3, trs2 = 1.0e-6)
dp..model dplcapmod =  (cjo = 4.6e-9, isl = 10e-30, nl=10, m = 0.9)
m..model mmedmod = (type=_n, vto = 3.05, kp = 2.5, is = 1e-30, tox = 1)
m..model mstrongmod = (type=_n, vto = 3.55, kp = 100, is = 1e-30, tox = 1)
m..model mweakmod = (type=_n, vto = 2.69, kp = 0.05, is = 1e-30, tox = 1, rs=0.1)
sw_vcsp..model s1amod =  (ron = 1e-5, roff = 0.1, von = -5.5, voff = -4.5)
sw_vcsp..model s1bmod =  (ron =1e-5, roff = 0.1, von = -4.5, voff = -5.5)
sw_vcsp..model s2amod =  (ron = 1e-5, roff = 0.1, von = -0.3, voff = 0.4)
sw_vcsp..model s2bmod =  (ron = 1e-5, roff = 0.1, von = 0.4, voff = -0.3)

c.ca n12 n8 = 6.6e-9
c.cb n15 n14 = 6.5e-9
c.cin n6 n8 = 3.8e-9

dp.dbody n7 n5 = model=dbodymod
dp.dbreak n5 n11 = model=dbreakmod
dp.dplcap n10 n5 = model=dplcapmod

i.it n8 n17 = 1

l.ldrain n2 n5 = 1.00e-9
l.lgate n1 n9 = 8.05e-9
l.lsource n3 n7 = 5.80e-9

m.mmed n16 n6 n8 n8 = model=mmedmod, l=1u, w=1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, l=1u, w=1u
m.mweak n16 n21 n8 n8 = model=mweakmod, l=1u, w=1u

res.rbreak n17 n18  = 1, tc1 = 1.27e-3, tc2 = 1.00e-6
res.rdrain n50 n16  = 5.0e-2, tc1 = 9.9e-3, tc2 =3.6e-5
res.rgate n9 n20 = 0.77
res.rldrain n2 n5 = 10
res.rlgate n1 n9 = 80.5
res.rlsource n3 n7 = 58
res.rslc1 n5 n51= 1e-6, tc1 = 3e-3, tc2 = -1.0e-6
res.rslc2 n5 n50 = 1e3
res.rsource n8 n7  = 1.8e-3, tc1 = 1.0e-3, tc2 =1e-6
res.rvtemp n18 n19  = 1, tc1 = -2.8e-3, tc2 = 1.70e-6
res.rvthres n22 n8  = 1, tc1 = -2.9e-3, tc2 = 1.1e-5

spe.ebreak n11 n7 n17 n18 = 221
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1
spe.evthres n6 n21 n19 n8 = 1

sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw_vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod

v.vbat n22 n19 = dc=1

equations {
i (n51->n50) +=iscl
iscl: v(n51,n50) = ((v(n5,n51)/(1e-9+abs(v(n5,n51))))*((abs(v(n5,n51)*1e6*100))** 2.5))
}
}
```



SPICE Thermal Model

REV May 2001

IRFP250N

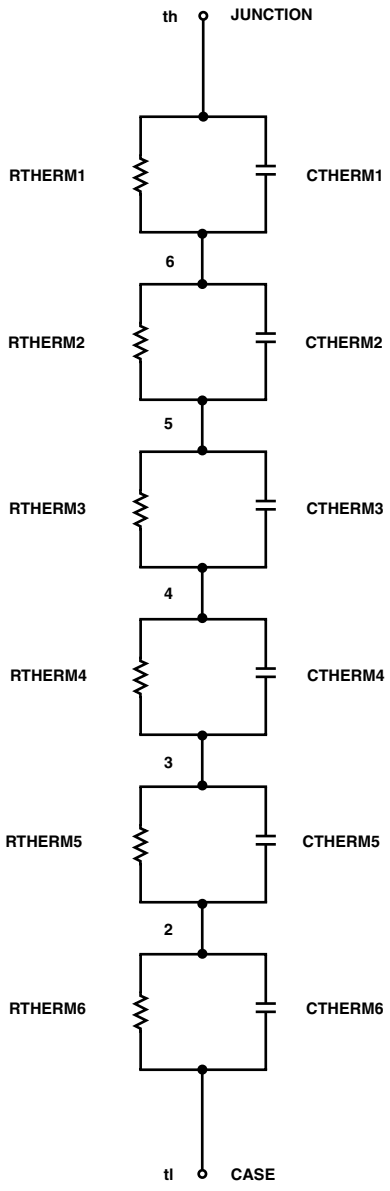
CTHERM1 th 6 6.45e-3
CTHERM2 6 5 3.00e-2
CTHERM3 5 4 1.40e-2
CTHERM4 4 3 1.65e-2
CTHERM5 3 2 4.85e-2
CTHERM6 2 tl 1.00e-1

RTHERM1 th 6 3.24e-3
RTHERM2 6 5 8.08e-3
RTHERM3 5 4 2.28e-2
RTHERM4 4 3 1.00e-1
RTHERM5 3 2 1.10e-1
RTHERM6 2 tl 1.40e-1

SABER Thermal Model

SABER thermal model IRFP250N

```
template thermal_model th tl
thermal_c th, tl
{
ctherm.ctherm1 th 6 = 6.45e-3
ctherm.ctherm2 6 5 = 3.00e-2
ctherm.ctherm3 5 4 = 1.40e-2
ctherm.ctherm4 4 3 = 1.65e-2
ctherm.ctherm5 3 2 = 4.85e-2
ctherm.ctherm6 2 tl = 1.00e-1

rtherm.rtherm1 th 6 = 3.24e-3
rtherm.rtherm2 6 5 = 8.08e-3
rtherm.rtherm3 5 4 = 2.28e-2
rtherm.rtherm4 4 3 = 1.00e-1
rtherm.rtherm5 3 2 = 1.10e-1
rtherm.rtherm6 2 tl = 1.40e-1
}
```



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CoolFET™	FRFET™	PACMAN™	Stealth™	
CROSSVOLT™	GlobalOptoisolator™	POP™	SuperSOT™-3	
DenseTrench™	GTO™	Power247™	SuperSOT™-6	
DOME™	HiSeC™	PowerTrench®	SuperSOT™-8	
EcoSPARK™	ISOPLANAR™	QFET™	SyncFET™	
E^2CMOS™	LittleFET™	QS™	TinyLogic™	
EnSigna™	MicroFET™	QT Optoelectronics™	TruTranslation™	
FACT™	MicroPak™	Quiet Series™	UHC™	
FACT Quiet Series™	MICROWIRE™	SILENT SWITCHER®	UltraFET®	

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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